

Resistivity, Sheet Resistance and Mobility

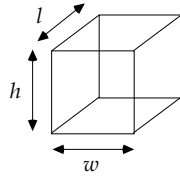
Overview

Topics:

- **Resistivity**
- **Sheet resistance**
- **Examples**
- **Conductivity and Electric Field**
- **Current Density**
- **Carrier concentration**
- **Mobility**

Resistivity

- Resistivity is the property of a material that determines the electrical resistance of a specific sample.



- The block of material has resistance (R) and resistivity (ρ).
- ρ remains constant regardless of size or shape.

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Resistivity

- Calculate resistance between front and back faces :

$$R = \rho \frac{l}{wh} = \rho \frac{l}{A}$$

- A is the area through which the current must pass and can be used where the cross-section is not rectangular, e.g. for a wire with circular cross-section.
- If length increases, resistance increases and vice versa. Opposite for area.
- The S.I. unit of resistivity is the $\Omega \cdot \text{m}$, but the practical unit is the $\Omega \cdot \text{cm}$.

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Sheet resistance

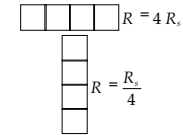
- In IC technology we often have conducting layers with constant depth (h in figure).
- Resistance therefore depends upon the aspect ratio as viewed from the surface (l/w).
- Define sheet resistance (R_s) so that resistance is:

$$R = R_s \frac{l}{w}$$

- R_s is given in Ω /square where $l = w$.

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Sheet Resistance



The relation between R and R_s is:

$$R_s \frac{l}{w} = R \frac{l}{l} \frac{w}{h}$$

But since $l = w$:

$$R = R_s \frac{w}{h}$$

Using sheet resistance, define resistance of an area (e.g. in a silicon IC) by number of squares.

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Example 1

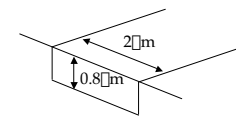
An aluminium rod 30cm long with a cross-section of 0.5cm x 0.25cm has a voltage of 100mV applied across it and a current of 13.9A is observed to flow. Calculate the resistivity, ρ , of the aluminium.

- $R = V/I = 0.1/13.9A = 7.2 \times 10^{-4} \Omega$
- $R = \rho l/wh$ or $\rho = Rwh/l$
so $\rho = 7.2 \times 10^{-4} \times 0.005 \times 0.0025/0.3 = 3 \times 10^{-8} \Omega \text{ m}$.

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Example 2

An area of undoped (high resistivity) silicon contains a region of doped silicon (so much lower resistivity) for fabricating a 20 k Ω resistor, as shown in the figure. If the resistivity, ρ , of the doped silicon is $10^{-3} \Omega \text{ m}$, calculate the sheet resistance, R_s , the number of squares of doped silicon required for the resistor, and hence the length of the resistor.



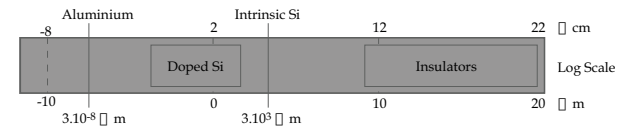
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Example 2 Solution

- We can assume that the doped silicon is a conducting area surrounded by insulator.
- $R_s = \rho/h = 10^{-3}/0.8 \times 10^{-6} = 1.25 \times 10^3 \Omega/\text{square} = 1.25\text{k}\Omega/\text{square}$.
- No of squares = aspect ratio l/w since all squares must have sides of length w (in this case $2\mu\text{m}$). $R = R_s l/w$ or $l/w = R/R_s$.
- No of squares = Value of resistor/ $R_s = 20\text{k}/1.25\text{k} = 16$ squares.
- Length of resistor = No of squares x length of side of a square = $16 \times 2\mu\text{m} = 32\mu\text{m}$.
- Alternatively to find the length:
 $R = R_s l/w$ or $l = R w/R_s = 20 \times 10^3 \times 2 \times 10^{-6} / 1.25 \times 10^3 = 32\mu\text{m}$.

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Range of Resistivity Values



Values cover 30 orders of magnitude!

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Conductivity and Electric Field

Conductivity

- The conductivity is the reciprocal of resistivity, i.e. the conductivity σ is given by:

$$\sigma = \frac{1}{\rho}$$

- The S.I. unit is obviously $\Omega^{-1} \text{m}^{-1}$, but the unit of conductance (Ω^{-1}) is the Siemen (S), so conductivity actually has unit S m^{-1} .

Electric Field

- The gradient of the potential.
- The electric field, E between two points distance l apart with potential difference V is:

$$E = \frac{V}{l}$$

- E has units of V m^{-1} .
- Also $E = -\frac{dV}{dx}$

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Current Density

- The current density is the current per unit area.
- If I is the total current flowing through an area A , the current density J is:

$$J = \frac{I}{A}$$

- J has units of A m^{-2} .

- Divide electric field by current density to get:

$$\frac{E}{J} = \frac{V/l}{I/A} = R \frac{A}{l}$$

$$\text{i.e. } \frac{E}{J} = R$$

- This is just a slightly different form of Ohm's Law.

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Electric Current

- Current is a flow of charge.
- We can measure current by measuring the charge that flows by in unit time ($I = Q/t$).
- Current is carried by charged particles (carriers) each carrying a known charge.
- Current is therefore determined by three factors:
 - The amount of charge on each carrier.
 - The number of charge carriers in unit volume (known as the carrier concentration or density).
 - The velocity of the charge carriers.

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Carrier Concentration

- Electric current carried by charged particles (positive or negative).
- Called carrier concentration n or p (depending whether the charge is negative or positive).
- S.I. unit for n and p is carriers/ m^3 (or simply m^{-3}).
- Practical unit used is cm^{-3} rather than the m^{-3} .

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Carrier Concentration

- Each carrier has charge.
- Negative charge carriers are electrons and charge is electronic charge ($q = 1.602 \times 10^{-19} \text{ C}$).
- Positive charge carriers have positive charge of same amount.
- Sometimes charge carriers have multiples of q , but not in normal conduction, and we will not consider these more unusual situations.

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Mobility

- Another important factor contributing to current.
- Carrier mobility (μ).
- Carriers accelerated by electric field, but decelerated again by collisions with atoms.
- Leads to a mean carrier velocity, \bar{v} , per applied electric field.
- The formula for mobility is:

$$\mu = \frac{\text{velocity}}{\text{electric field}} = \frac{\bar{v}}{E}$$

- Units are $\text{m}^2 \text{v}^{-1} \text{s}^{-1}$. Practical unit is $\text{cm}^2 \text{v}^{-1} \text{s}^{-1}$.

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